





60V N-CHANNEL ENHANCEMENT MODE VERTICAL DMOSFET IN SOT23

Features

- $BV_{DSS} > 60V$
- $R_{DS(on)} \le 2.5\Omega$ @ $V_{GS} = 10V$
- Maximum continuous drain current I_D = 200mA
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

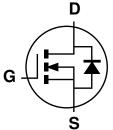
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish. Solderable per MIL-STD-202, Method
- Weight: 0.008 grams (approximate)

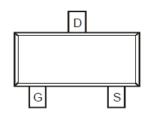








Device symbol



Pin-Out Top View

Ordering Information (Note 4)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZVN4106FTA	MZ	7	8	3000

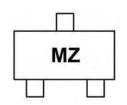
Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

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- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com.

Marking Information



MZ = Product Type Marking Code



ZVN4106F

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	60	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current	ID	200	mA
Pulsed Drain Current (Note 5)	I _{DM}	3	Α

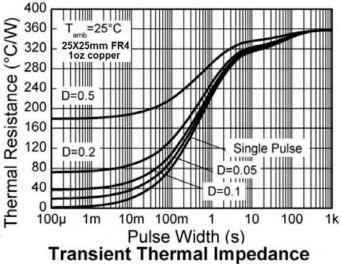
Thermal Characteristics

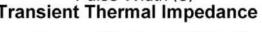
Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 6)	P_{D}	350	mW
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{ heta JA}$	357	°C/W
Operating and Storage Temperature Range		T_J , T_{STG}	-55 to +150	°C

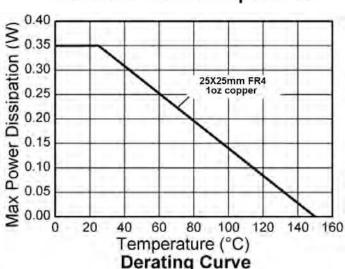
Notes:

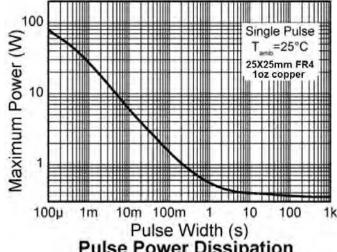
- 5. Device mounted on minimum recommended pad layout test board, 10 s pulse duty cycle = 1%.
- 6. For a device mounted on 25mm X 25mm X 1.6mm FR-4 PCV with high coverage of single sided 1oz copper, in still air condition.

Thermal Characteristics



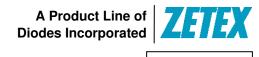






Pulse Power Dissipation





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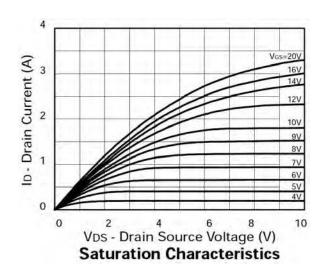
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

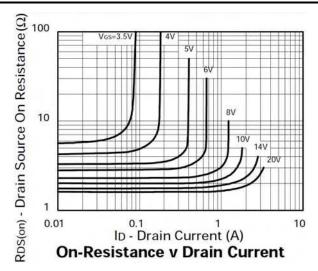
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	_		V	$V_{GS} = 0V$, $I_D = 10mA$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	l	_	10 50	μΑ	$V_{DS} = 60V, V_{GS} = 0V$ $V_{DS} = 48V, V_{GS} = 0V, T_A = +125^{\circ}C$	
Gate-Source Leakage	I _{GSS}		_	100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
On-State Drain Current	I _{D(on)}	1	_	-	Α	$V_{GS} = 10V, V_{DS} = 15V$	
ON CHARACTERISTICS (Note 7)			ā.				
Gate Threshold Voltage	V _{GS(th)}	1.3	_	3	V	$V_{DS} = V_{GS}$, $I_D = 1mA$	
Static Drain-Source On-Resistance	R _{DS (on)}		_	2.5 5	Ω	$V_{GS} = 10V, I_D = 500mA$ $V_{GS} = 5V, I_D = 200mA$	
Forward Transconductance		150	_	-	mS	V _{DS} = 25V, I _D = 250mA	
DYNAMIC CHARACTERISTICS (Note 7)	0.0						
Input Capacitance	C _{iss}	1	_	35	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz	
Output Capacitance	Coss	_	_	25	pF		
Reverse Transfer Capacitance	C _{rss}	_	_	8	pF		
Turn-On Delay Time	t _{D(on)}	_	_	5	ns	V _{DS} = 25V, I _D = 150mA	
Turn-On Rise Time	t _r	_	_	7	ns		
Turn-Off Delay Time	t _{D(off)}	_	_	6	ns		
Turn-Off Fall Time	t _f		—	8	ns		

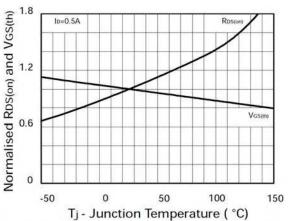
Notes: 7. Short duration pulse test used to minimize self-heating effect.

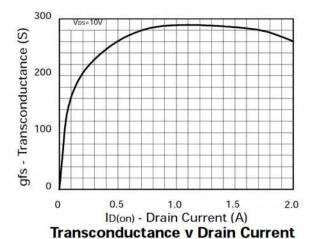


Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

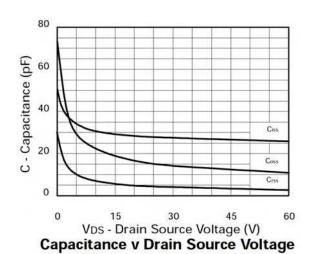


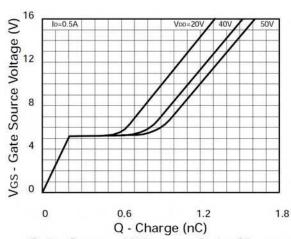






Normalised RDS(on) & VGS(th) v Temperature

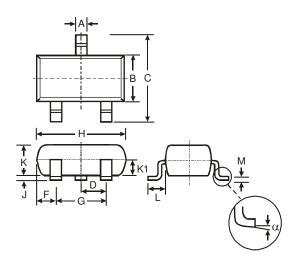




Gate Source Voltage v Gate Charge

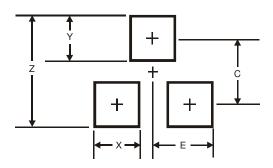


Package Outline Dimensions



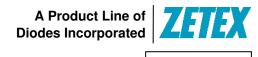
SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
K	0.903	1.10	1.00		
K1	-	-	0.400		
L	0.45	0.61	0.55		
M	0.085	0.18	0.11		
α	0°	8°	-		
All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
E	1.35





ZVN4106F

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